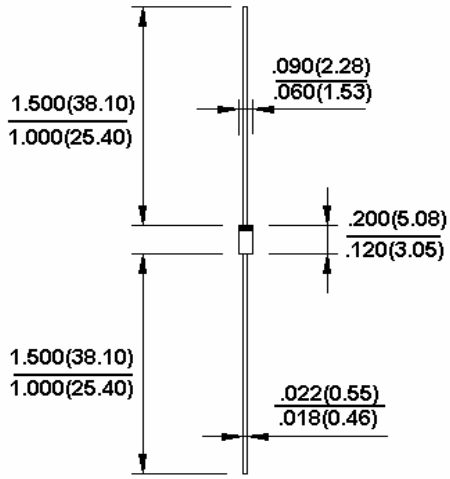
1N4448/1N4148/1N914B

500 mW Hermetically Sealed Glas Fast Switching Diodes

DO-35

Features

- ✧ Fast switching device (T_{RR}<4.0nS)
- ✧ DO-35 package (JEDEC)
- ✧ Through-hole device type mounting
- ✧ Hermetically sealed glass
- ✧ Compression bonded construction
- ✧ All external surface are corrosion resistant and leads are readily solderable
- ✧ RoHS compliant
- ✧ Solder hot dip Tin(Sn) lead finish
- ✧ Cathode indicated by polarity band



Dimensions in inches and(millimeters)

Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified.

Maximum Ratings

Type Number	Symbol	Value	Units
Power Dissipation	Pd	500	mW
Working Inverse Voltage	W_{IV}	75	V
Non-repetitive Peak Forward Current	I_{FM}	450	mA
Average Rectified Current	Io	150	mA
Peak Forward Surge Current	I_{FSURGE}	2	A
Operating Junction Temperature	T_J	175	°C
Storage Temperature Range	T_{STG}	-65 to + 200	°C

Electrical Characteristics

Type Number		Symbol	Min	Max	Units
Breakdown Voltage	IR=100uA IR=5uA	B_V	100 75		V
Forward Voltage 1N4448, 1N914B 1N4148 1N4448, 1N914B	IF=5.0mA IF= 10mA IF =100mA	V_F	0.62	0.72 1.0 1.0	V
Reverse Leakage Current	VR=20V VR=75V	I_R		25 5	nA uA
Junction Capacitance	VR=0, f=1.0MHz	Cj	-	4.0	pF
Reverse Recovery Time (Note 1)		trr	-	4.0	nS

Notes: 1. Reverse Recovery Test Conditions: I_F=10mA, VR=6V, R_L=100Ω, I_{RR}=1mA

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RATINGS AND CHARACTERISTIC CURVES **(1N4448/1N4148/1N914B)**

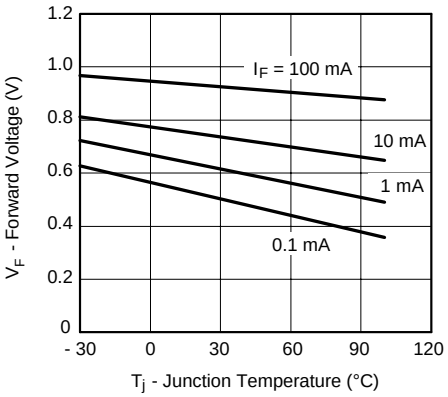

Figure 1. Forward Voltage vs. Junction Temperature

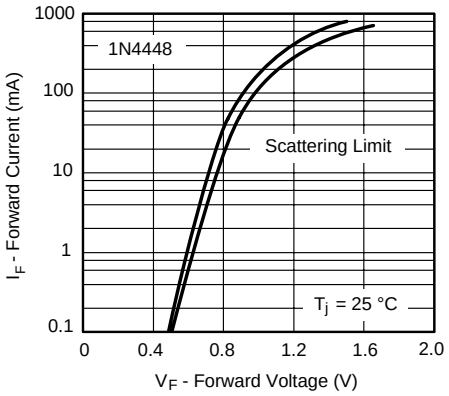

Figure 3. Forward Current vs. Forward Voltage

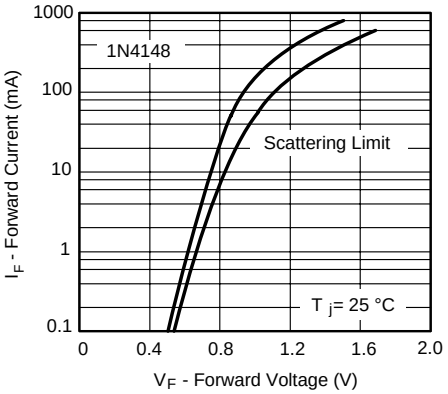

Figure 2. Forward Current vs. Forward Voltage

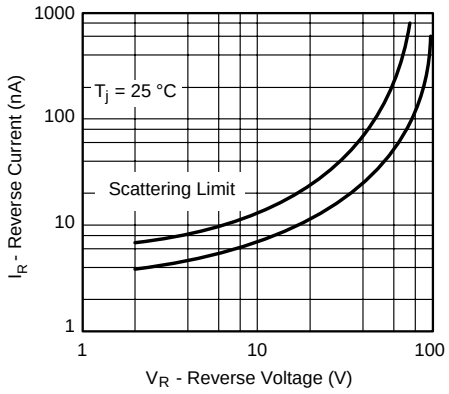

Figure 4. Reverse Current vs. Reverse Voltage